

# BC556B, BC557A, B, C, BC558B

## Amplifier Transistors

### PNP Silicon

#### Features

- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage BC556 BC557 BC558	$V_{CEO}$	-65 -45 -30	Vdc
Collector - Base Voltage BC556 BC557 BC558	$V_{CBO}$	-80 -50 -30	Vdc
Emitter - Base Voltage	$V_{EBO}$	-5.0	Vdc
Collector Current – Continuous – Peak	$I_C$ $I_{CM}$	-100 -200	mAdc
Base Current – Peak	$I_{BM}$	-200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

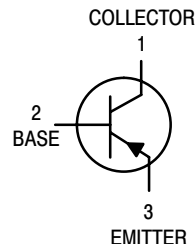
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

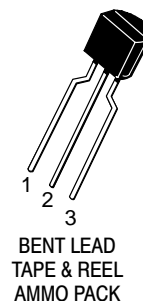
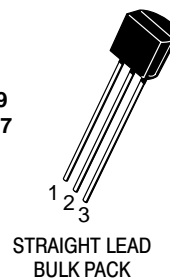


ON Semiconductor®

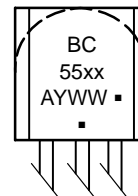
<http://onsemi.com>



TO-92  
CASE 29  
STYLE 17



#### MARKING DIAGRAM



xx = 6B, 7A, 7B, 7C, or 8B  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

# BC556B, BC557A, B, C, BC558B

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage ( $I_C = -2.0\text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-65 -45 -30	– – –	– – –	V
Collector–Base Breakdown Voltage ( $I_C = -100\text{ }\mu\text{Adc}$ )	$V_{(BR)CBO}$	-80 -50 -30	– – –	– – –	V
Emitter–Base Breakdown Voltage ( $I_E = -100\text{ }\mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-5.0 -5.0 -5.0	– – –	– – –	V
Collector–Emitter Leakage Current ( $V_{CES} = -40\text{ V}$ ) ( $V_{CES} = -20\text{ V}$ )  ( $V_{CES} = -20\text{ V}$ , $T_A = 125^\circ\text{C}$ )	$I_{CES}$	– – – – – –	-2.0 -2.0 -2.0 – – –	-100 -100 -100 -4.0 -4.0 -4.0	nA     $\mu\text{A}$

## ON CHARACTERISTICS

DC Current Gain ( $I_C = -10\text{ }\mu\text{Adc}$ , $V_{CE} = -5.0\text{ V}$ )  ( $I_C = -2.0\text{ mAdc}$ , $V_{CE} = -5.0\text{ V}$ )  ( $I_C = -100\text{ mAdc}$ , $V_{CE} = -5.0\text{ V}$ )	A Series Device B Series Devices C Series Devices BC557 A Series Device B Series Devices C Series Devices A Series Device B Series Devices C Series Devices	$h_{FE}$	– – – 120 120 180 420 – – –	90 150 270 – 170 290 500 120 180 300	– – – 800 220 460 800 – – –	–
Collector–Emitter Saturation Voltage ( $I_C = -10\text{ mAdc}$ , $I_B = -0.5\text{ mAdc}$ ) ( $I_C = -10\text{ mAdc}$ , $I_B = \text{see Note 1}$ ) ( $I_C = -100\text{ mAdc}$ , $I_B = -5.0\text{ mAdc}$ )		$V_{CE(sat)}$	– – –	-0.075 -0.3 -0.25	-0.3 -0.6 -0.65	V
Base–Emitter Saturation Voltage ( $I_C = -10\text{ mAdc}$ , $I_B = -0.5\text{ mAdc}$ ) ( $I_C = -100\text{ mAdc}$ , $I_B = -5.0\text{ mAdc}$ )		$V_{BE(sat)}$	– –	-0.7 -1.0	– –	V
Base–Emitter On Voltage ( $I_C = -2.0\text{ mAdc}$ , $V_{CE} = -5.0\text{ Vdc}$ ) ( $I_C = -10\text{ mAdc}$ , $V_{CE} = -5.0\text{ Vdc}$ )		$V_{BE(on)}$	-0.55 –	-0.62 -0.7	-0.7 -0.82	V

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ( $I_C = -10\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ , $f = 100\text{ MHz}$ )	BC556 BC557 BC558	$f_T$	– – –	280 320 360	– – –	MHz
Output Capacitance ( $V_{CB} = -10\text{ V}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )		$C_{ob}$	–	3.0	6.0	pF
Noise Figure ( $I_C = -0.2\text{ mAdc}$ , $V_{CE} = -5.0\text{ V}$ , $R_S = 2.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $\Delta f = 200\text{ Hz}$ )	BC556 BC557 BC558	NF	– – –	2.0 2.0 2.0	10 10 10	dB
Small–Signal Current Gain ( $I_C = -2.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ V}$ , $f = 1.0\text{ kHz}$ )	BC557 A Series Device B Series Devices C Series Devices	$h_{fe}$	125 125 240 450	– – – –	900 260 500 900	–

1.  $I_C = -10\text{ mAdc}$  on the constant base current characteristics, which yields the point  $I_C = -11\text{ mAdc}$ ,  $V_{CE} = -1.0\text{ V}$ .

# BC556B, BC557A, B, C, BC558B

## BC557/BC558

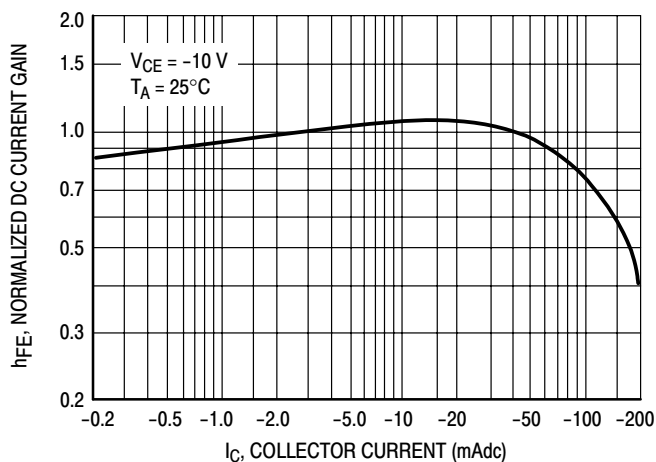


Figure 1. Normalized DC Current Gain

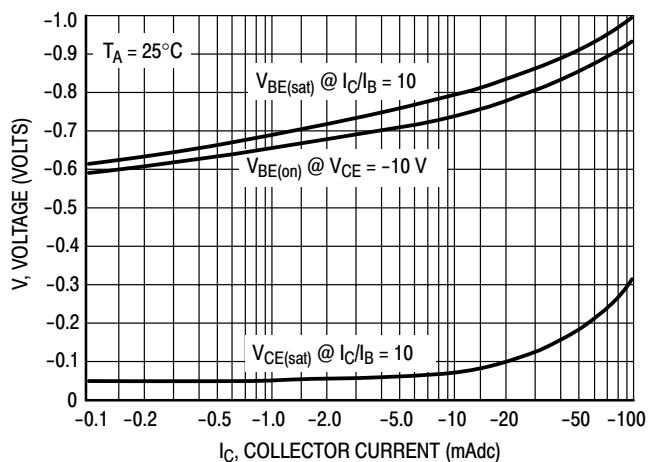


Figure 2. "Saturation" and "On" Voltages

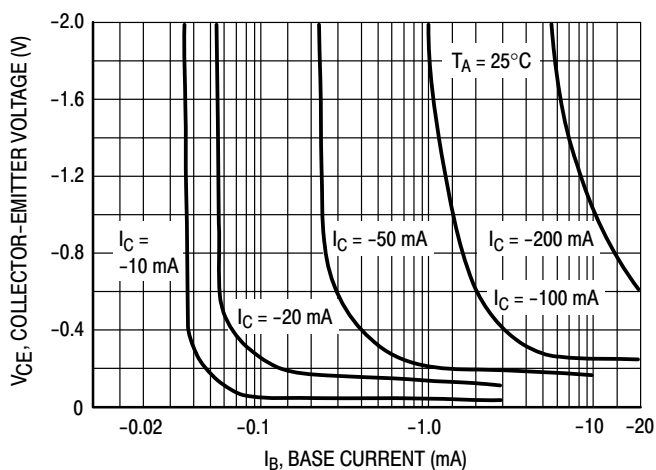


Figure 3. Collector Saturation Region

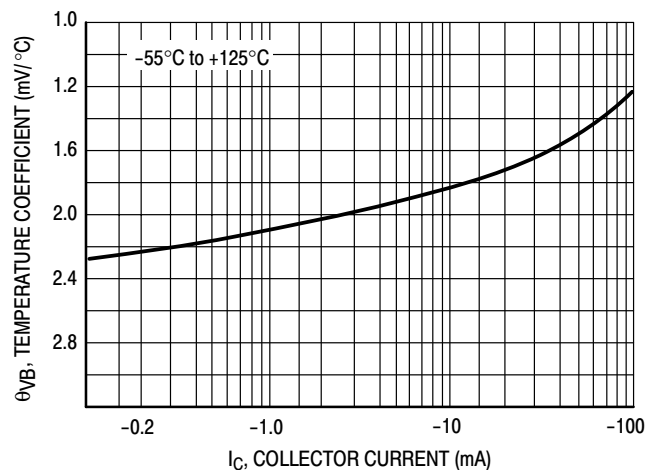


Figure 4. Base-Emitter Temperature Coefficient

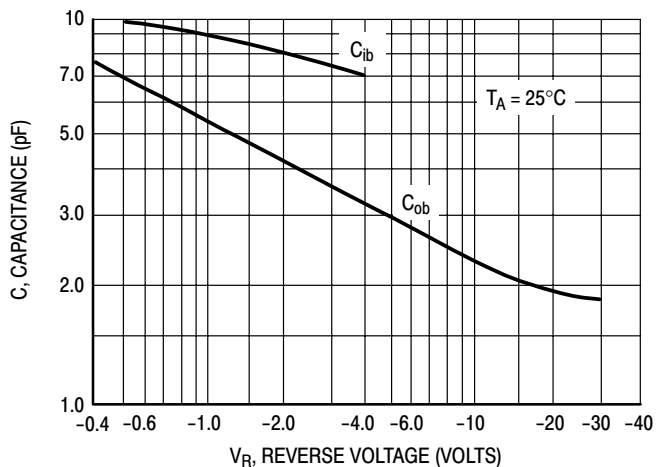


Figure 5. Capacitances

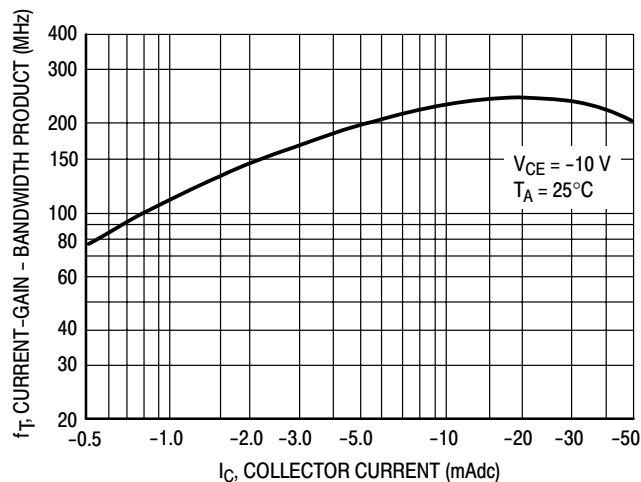


Figure 6. Current-Gain - Bandwidth Product

BC556

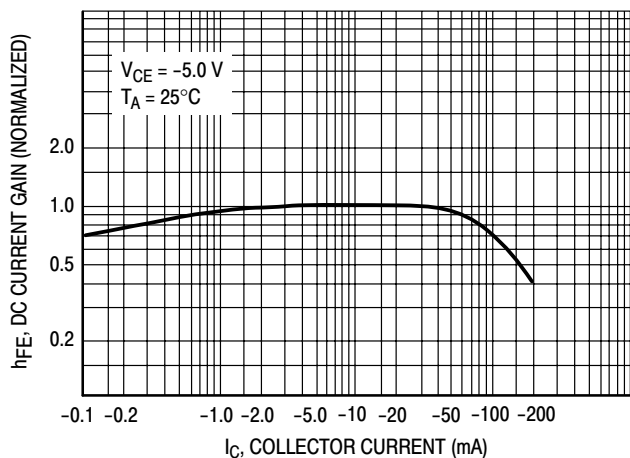


Figure 7. DC Current Gain

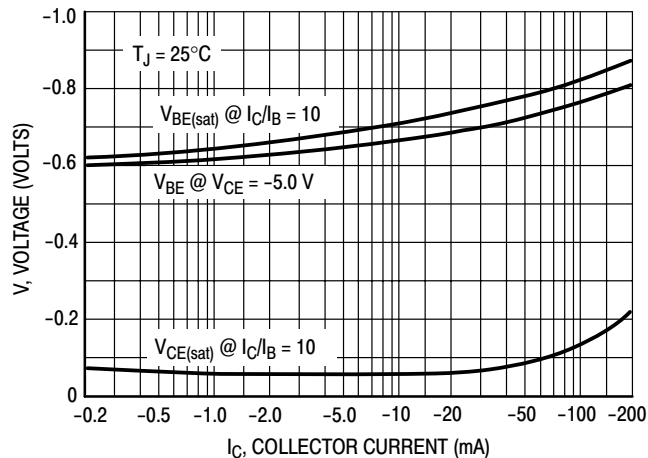


Figure 8. "On" Voltage

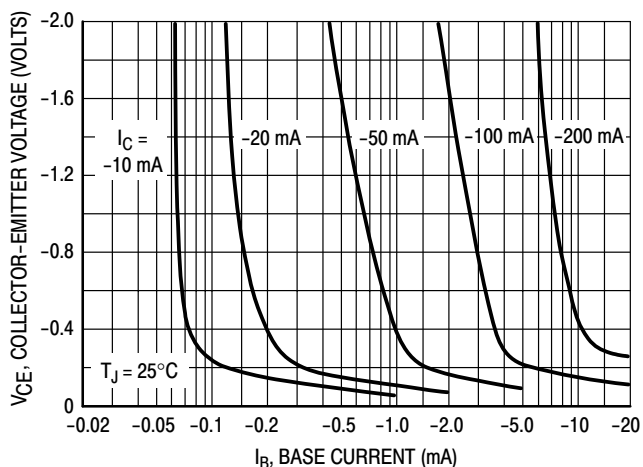


Figure 9. Collector Saturation Region

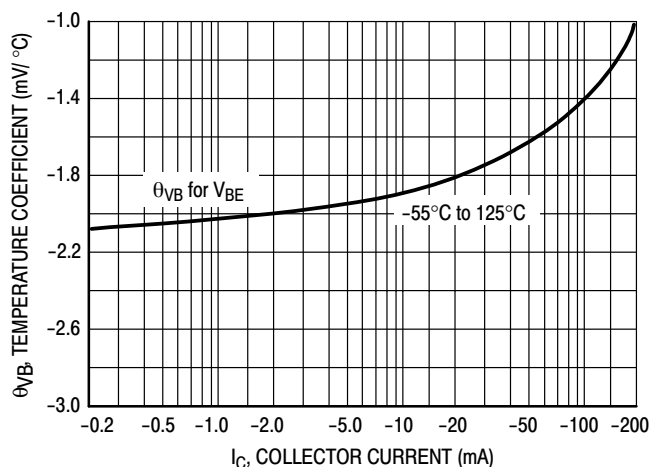


Figure 10. Base-Emitter Temperature Coefficient

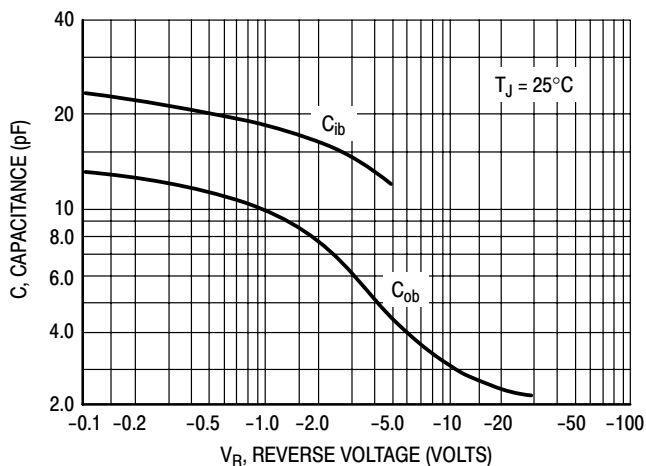


Figure 11. Capacitance

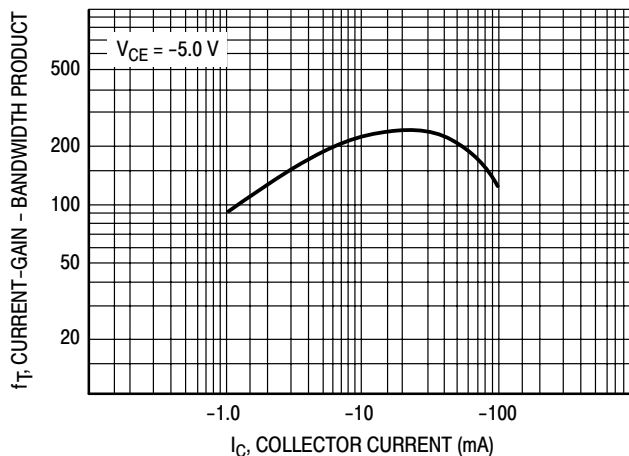


Figure 12. Current-Gain - Bandwidth Product

# BC556B, BC557A, B, C, BC558B

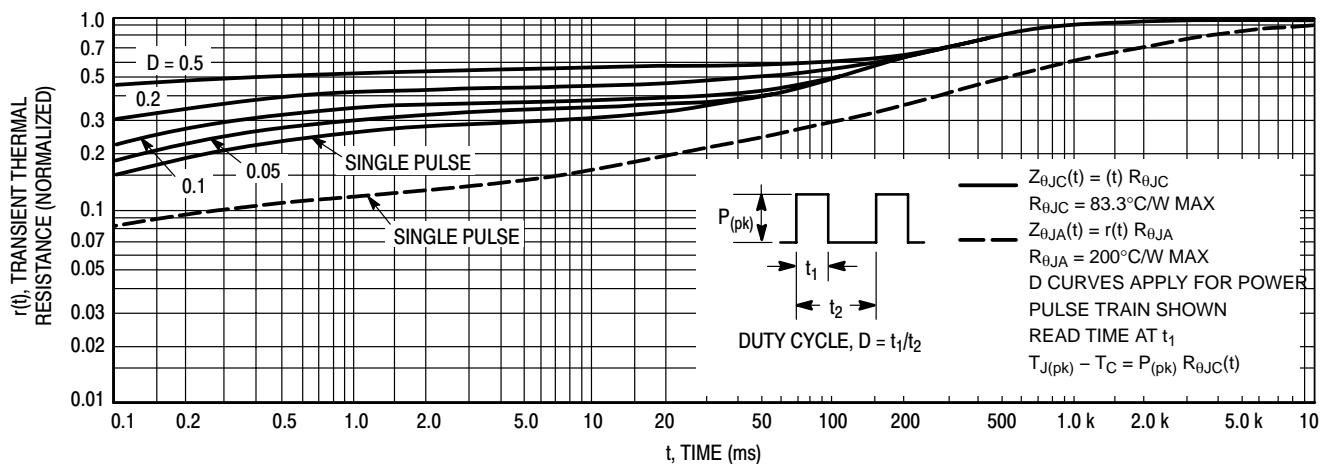


Figure 13. Thermal Response

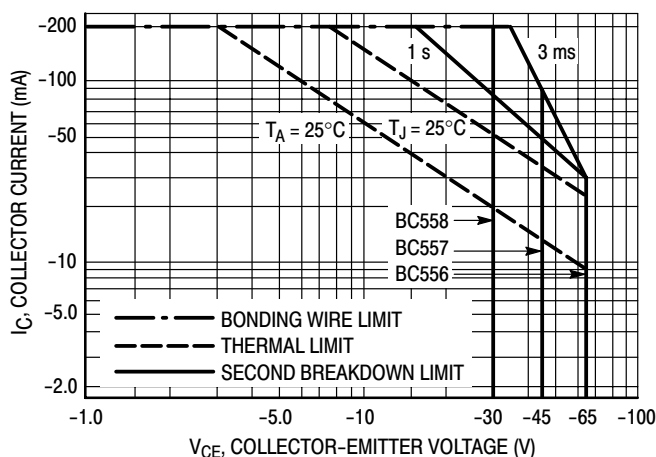


Figure 14. Active Region - Safe Operating Area

The safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  or  $T_A$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

## BC556B, BC557A, B, C, BC558B

### ORDERING INFORMATION

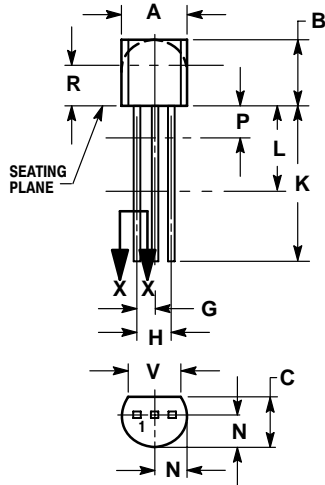
Device	Package	Shipping†
BC556BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC556BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557AZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557BRL1	TO-92	2000 / Tape & Reel
BC557BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC557BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC558BRLG	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

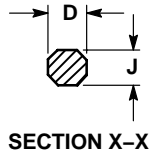
# BC556B, BC557A, B, C, BC558B

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AM



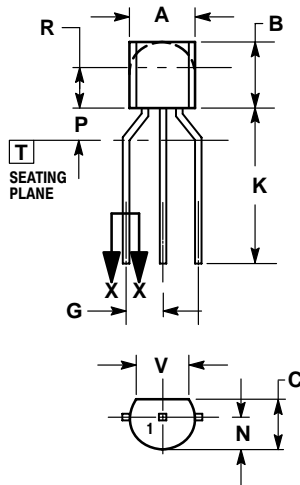
STRAIGHT LEAD  
BULK PACK



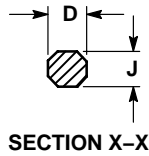
### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK




### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

### STYLE 17:

1. COLLECTOR
2. BASE
3. EMITTER

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
Email: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

N. American Technical Support: 800-282-9855 Toll Free  
USA/Canada  
Europe, Middle East and Africa Technical Support:  
Phone: 421 33 790 2910  
Japan Customer Focus Center  
Phone: 81-3-5773-3850

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative